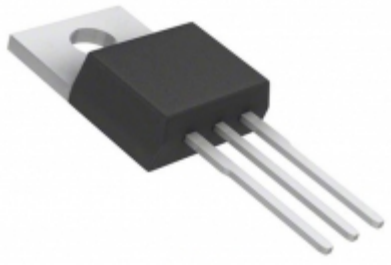








	<h2 style="color: red;">FQP13N06L</h2>
	<p>Hersteller-Teilenummer: FQP13N06L</p> <p>Hersteller / Marke: Fairchild/ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 60V 13.6A TO-220</p> <p>Datenblätter: 1.FQP13N06L.pdf 2.FQP13N06L.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 49007 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQP13N06L
Hersteller	Fairchild/ON Semiconductor
Beschreibung	MOSFET N-CH 60V 13.6A TO-220
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	49007 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3
Supplier Device-Gehäuse	TO-220-3
Verlustleistung (max)	45W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	13.6A (Tc)
Rds On (Max) @ Id, Vgs	110 mOhm @ 6.8A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	6.4nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	350pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	5V, 10V
Vgs (Max)	±20V
Verpackung	Tube

FQP13N06L ist neu im Original, Suche FQP13N06L Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQP13N06L Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQP13N06L: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQP13N10C FSC FQP13N10C FSC</p>	 <p>FQP13N06 Fairchild/ON Semiconductor MOSFET N-CH 60V 13A TO-220</p>	 <p>FQP13N10 AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12.8A TO-220</p>	 <p>FQP13N10L AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 12.8A TO-220</p>
 <p>FQP13N06L FQP13N06 Original FQP13N06L FQP13N06 Original</p>	 <p>FQP13N06 AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 13A TO-220</p>	 <p>FQP13N06L AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 13.6A TO-220</p>	 <p>FQP13N10 Fairchild/ON Semiconductor MOSFET N-CH 100V 12.8A TO-220</p>

heiße Teile

Mehr

⊗ FQP10N60C_07	↔ FQP10N65	⇒ FQP10N65C	D FQP10N80	⇒ FQP11N40C
⊣ FQP11N40C	⊗ FQP11N50CF	D FQP11N50CF	⇒ FQP11N60	⇒ FQP11N60C
⊗ FQP11N65C	⊣ FQP11P06	⊗ FQP11P06	↔ FQP12N20	⇒ FQP12N60
D FQP12N60	⊗ FQP12N60C	⊣ FQP12N60C	⊗ FQP12N65C	⇒ FQP12P10
⇒ FQP12P10	↔ FQP12P20	⊗ FQP12P20	⊣ FQP13N06	⇒ FQP13N06
↔ FQP13N06L	⇒ FQP13N10	D FQP13N10	⊗ FQP13N10L	⊣ FQP13N10L
⊗ FQP13N50	D FQP13N50	⇒ FQP13N50C	↔ FQP13N50C	⇒ FQP13N60C
⊣ FQP140N03	⊗ FQP140N03L	↔ FQP14N15	⇒ FQP14N15	⇒ FQP14N30
⊗ FQP14N30	⊣ FQP14N80	⊗ FQP14N80C	D FQP15N16	⇒ FQP15N30
↔ FQP15N50	⊗ FQP15N60	⊣ FQP15N65	⊗ FQP15N80	⇒ FQP15P12

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